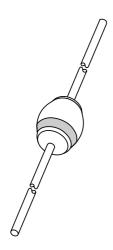
DISCRETE SEMICONDUCTORS

DATA SHEET



BYV99 Ultra fast low-loss controlled avalanche rectifier

Product specification Supersedes data of 1996 Feb 19

2003 Mar 04





Ultra fast low-loss controlled avalanche rectifier

BYV99

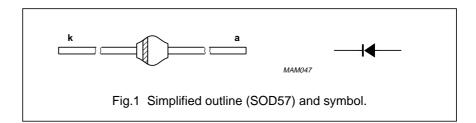
FEATURES

- · Glass passivated
- · Low leakage current
- · Excellent stability
- Guaranteed avalanche energy absorption capability
- Available in ammo-pack.

DESCRIPTION

Rugged glass SOD57 package, using a high temperature alloyed construction.

This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER CONDITIONS		MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage		_	600	V
V _R	continuous reverse voltage		_	600	V
I _{F(AV)}	average forward current	T _{tp} = 50 °C; lead length = 10 mm; see Fig.2; averaged over any 20 ms period; see also Fig.6	_	1	A
		T _{amb} = 60 °C; see Fig.3; PCB mounting (see Fig.11); averaged over any 20 ms period; see also Fig.6	_	0.55	A
I _{FRM}	repetitive peak forward current	T _{tp} = 50 °C; see Fig.4	_	9	А
		T _{amb} = 60 °C; see Fig.5	_	5	А
I _{FSM}	non-repetitive peak forward current	$t = 10$ ms half sine wave; $T_j = T_{j(max)}$ prior to surge; $V_R = V_{RRMmax}$	_	20	А
E _{RSM}	non-repetitive peak reverse avalanche energy	L = 120 mH; $T_j = T_{j(max)}$ prior to surge; inductive load switched off	_	10	mJ
T _{stg}	storage temperature		-65	+175	°C
T _j	junction temperature	see also Fig.10	-65	+150	°C

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ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	forward voltage	$I_F = 1 \text{ A}; T_j = T_{j(max)}; \text{ see Fig.7}$	_	_	1.5	V
		I _F = 1 A; see Fig.7	_	_	2.7	V
V _{(BR)R}	reverse avalanche breakdown voltage	I _R = 0.1 mA	700	_	_	V
I _R	reverse current	V _R = V _{RRMmax} ; see Fig.8	_	_	5	μΑ
		$V_R = V_{RRMmax}$; $T_j = 150 ^{\circ}C$; see Fig.8	_	_	75	μΑ
t _{rr}	reverse recovery time	when switched from $I_F = 0.5$ A to $I_R = 1$ A; measured at $I_R = 0.25$ A; see Fig.13	_	_	15	ns
C _d	diode capacitance	f = 1 MHz; V _R = 0 V; see Fig.9	_	75	_	pF
$\left \frac{dI_R}{dt} \right $	maximum slope of reverse recovery current	when switched from $I_F = 1$ A to $V_R \ge 30$ V and $dI_F/dt = -1$ A/ μ s; see Fig.12	_	_	3	A/μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point	lead length = 10 mm	46	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	100	K/W

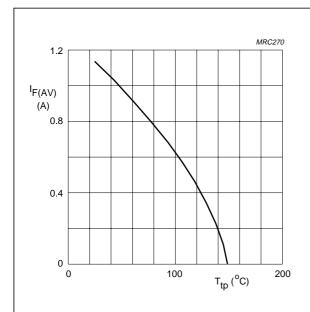
Note

^{1.} Device mounted on an epoxy-glass printed-circuit board, 1.5 mm thick; thickness of Cu-layer ≥40 μm; see Fig.11. For more information please refer to the "General Part of associated Handbook".

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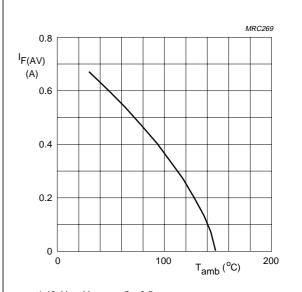
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GRAPHICAL DATA



 $a = 1.42; \ V_R = V_{RRMmax}; \ \delta = 0.5.$ Switched mode application.

Fig.2 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).

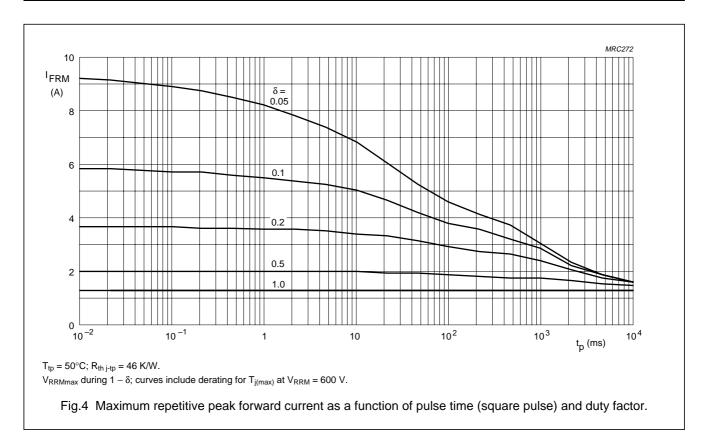


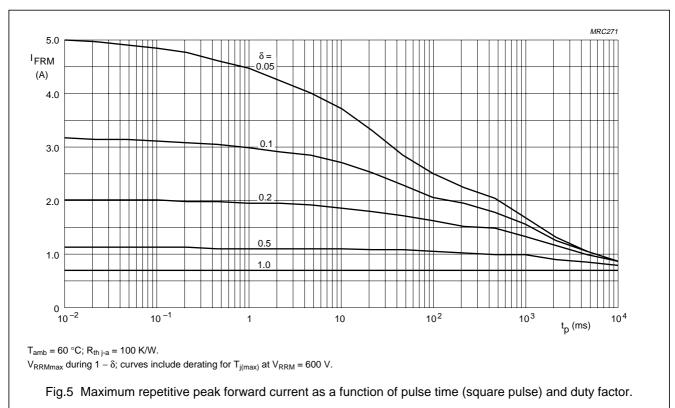
 $a=1.42;\ V_R=V_{RRMmax};\ \delta=0.5.$ Device mounted as shown in Fig.11. Switched mode application.

Fig.3 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).

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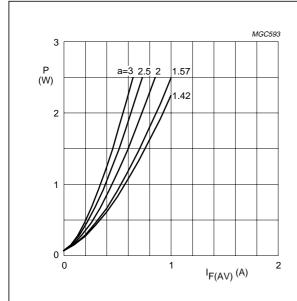
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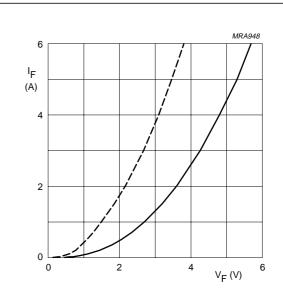
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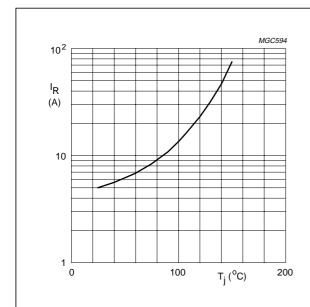
 $a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$; $\delta = 0.5$.

Fig.6 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.



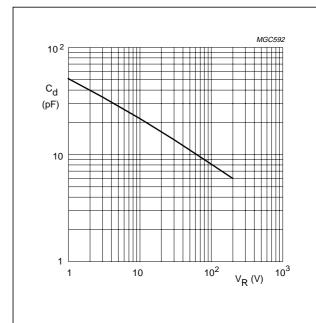
Dotted line: $T_j = 150 \,^{\circ}\text{C}$. Solid line: $T_j = 25 \,^{\circ}\text{C}$.

Fig.7 Forward current as a function of forward voltage; maximum values.



 $V_R = V_{RRMmax}$

Fig.8 Reverse current as a function of junction temperature; maximum values.



f = 1 MHz; T_i = 25 °C.

Fig.9 Diode capacitance as a function of reverse voltage; typical values.

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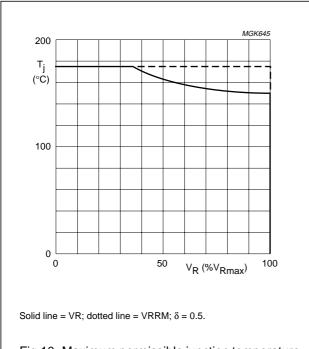
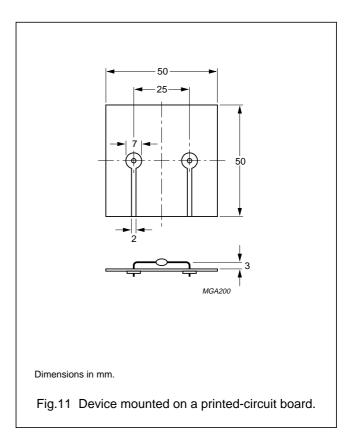
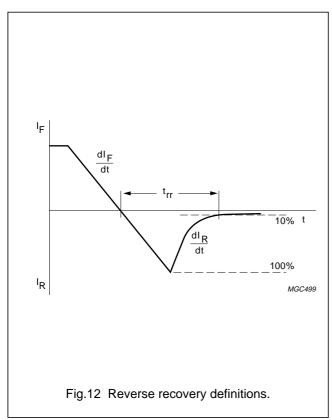


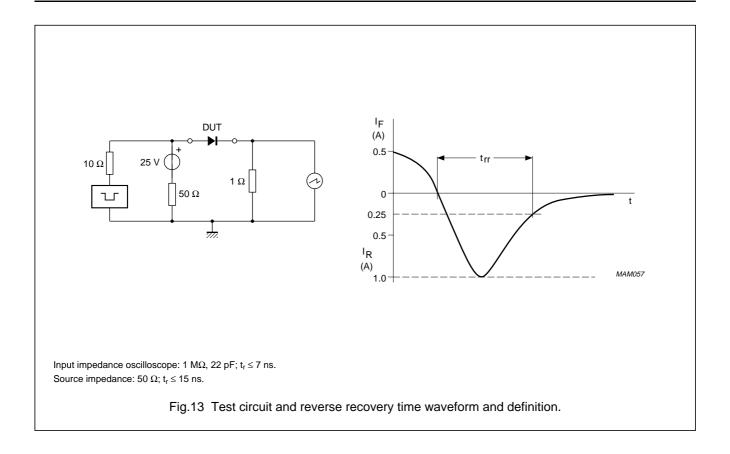
Fig.10 Maximum permissible junction temperature as a function of maximum reverse voltage percentage.





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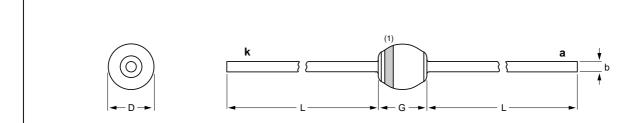
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PACKAGE OUTLINE

Hermetically sealed glass package; axial leaded; 2 leads

SOD57



DIMENSIONS (mm are the original dimensions)

UNIT	b max.	D max.	G max.	L min.
mm	0.81	3.81	4.57	28

0 2.5 5 mm scale

Note

1. The marking band indicates the cathode.

OUTLINE		REFER	RENCES	EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ	PROJECTION	1330E DATE	
SOD57					97-10-14	

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

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- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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2003 Mar 04

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NOTES

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